

# NPN SILICON RF POWER TRANSISTOR

**DESCRIPTION:**

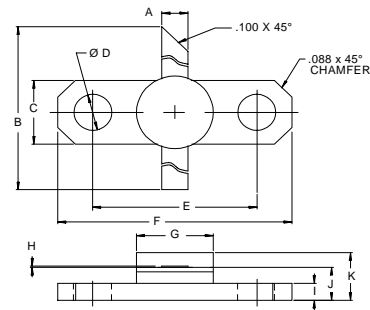
The **ASI AVF100** is Designed for Class C, IFF Applications up to 1090 MHz.

**FEATURES:**

- Internal Input/Output Matching Networks
- $P_G = 10$  dB at 100 W/1090 MHz
- **Omnigold™** Metalization System

**MAXIMUM RATINGS**

$I_C$	10 A
$V_{CB}$	60 V
$V_{CE}$	35 V
$P_{DISS}$	140 W @ $T_C = 25^\circ\text{C}$
$T_J$	-65 °C to +200 °C
$T_{STG}$	-65 °C to +150 °C
$\theta_{JC}$	35 °C/W

**PACKAGE STYLE .250 2L FLG (B)**


DIM	MINIMUM inches / mm	MAXIMUM inches / mm
A	.095 / 2.41	.105 / 2.67
B	1.050 / 26.67	
C	.245 / 6.22	.255 / 6.48
D	.120 / 3.05	.140 / 3.56
E	.552 / 14.02	.572 / 14.53
F	.790 / 20.07	.810 / 20.57
G		.285 / 7.24
H	.003 / 0.08	.007 / 0.18
I	.052 / 1.32	.072 / 1.83
J	.120 / 3.05	.130 / 3.30
K		.210 / 5.33

**ORDER CODE: ASI10569**
**CHARACTERISTICS**  $T_C = 25^\circ\text{C}$ 

SYMBOL	TEST CONDITIONS	MINIMUM	TYPICAL	MAXIMUM	UNITS
$BV_{CEO}$	$I_C = 50$ mA	35			V
$BV_{CER}$	$I_C = 50$ mA $R_{BE} = 10 \Omega$	60			V
$BV_{EBO}$	$I_E = 10$ mA	4.0			V
$I_{CES}$	$V_{CE} = 28$ V			5.0	mA
$h_{FE}$	$V_{CE} = 5.0$ V $I_C = 1.0$ A	10		100	---
$C_{ob}$	$V_{CB} = 28$ V $f = 1.0$ MHz			80	pF
$P_G$ $\eta_C$	$V_{CC} = 40$ V $P_{OUT} = 100$ W $f = 1030 - 1090$ MHz	10 35			dB %

This datasheet has been download from:

[www.datasheetcatalog.com](http://www.datasheetcatalog.com)

Datasheets for electronics components.